## NSN 5961-01-100-4472



Transistor - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-100-4472 **Inclosure Material:** Metal **Overall Length:** Between 0.250 inches and 0.450 inches Overall Diameter: 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 breakdown voltage, collector-to-emitter, base open and 550.0 collector to emitter voltage, dc with specified circuit between base and emitter and 700.0 collector to emitter reverse voltage and 8.0 emitter to base voltage, dc and 500.0 breakdown voltage, collector to emitter, sustained **Current Rating Per Characteristic:** Between 10.00 amperes source cutoff current and 50.00 amperes source cutoff current **Power Rating Per Characteristic:** 250.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Test Data Document:** 96214-804363 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a **Unit Of Measure:** 

Fiig:

No

Demilitarization: